



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:  
**CROCE ET AL.**

Serial No. **09/839,596** ✓

Confirmation No. **1496**

Filing Date: **April 20, 2001** ✓

For: **RESURF LDMOS INTEGRATED  
STRUCTURE**

) Examiner: O. Nadav

) Art Unit: 2811

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NOV 29 2002  
TC 2800 MAIL ROOM

#11/B  
And  
N/E  
J. Williams  
12/20/02

AMENDMENT

Director, U.S. Patent and Trademark Office  
Washington, D.C. 20231

Sir:

Responsive to the Office Action of August 21, 2002,  
please enter the amendments and remarks set out below.

In the Specification:

Please replace the paragraph beginning at page 4,  
line 30, with the following rewritten paragraph:

B1

The present invention provides a relatively simple and effective solution to punch-through (PT) problems that normally limit the performance of known RESURF LDMOS structures when functioning as high side drivers. This is done without introducing substantial changes in the known RESURF LDMOS structure. The invention is directed to a RESURF LDMOS structure that includes a superficial or surface portion (or body buffer region) **15** of the drain well region **12** which surrounds the body region **13**. The body buffer region **15** is preferably more heavily doped than the remaining portion of the drain well region **12**, as shown in FIG. 2b. In the drawings, like numbers are used throughout to refer to similar elements for clarity of illustration.